



DATASHEET

● ● ● 25 Gbit/s VCSEL and VCSEL array chips (850 nm) ● ● ● ● ● ● ● ● ● ●

Product code:

CO-V850-25-1 1x1 chip
CO-V850-25-4 1x4 array
CO-V850-25-12 1x12 array



Product Description

These compact and very high modulation rate top-emitting GaAs-based vertical cavity surface emitting laser (VCSEL) chips and 1xN ($N=1, 2, 4, 12$, etc.) arrays are available as engineering samples for use in the development and evaluation of optical interconnects, optical backplanes and integrated waveguides, and next-generation optical data communications systems. The VCSELs are contacted on the top-surface individually using ground-source (GS) microprobes, wire bonds, or flip-chip bonds.

Features

- Up to 12 parallel channels
 - More than 25 Gbit/s per channel
 - High temperature stability
 - A device-to-device pitch of 250 µm
 - Suitable for wire or flip-chip bonding

Applications

- Active optical cables (AOCs), TOSA
 - High-speed optical interconnects and links
 - Infiniband EDR (eight data rate), Radio-over-Fiber, Fibre Channel and short-reach 40/100 Gbit/s Ethernet
 - Chip-to-chip interconnects

Optical and Electrical Characteristics

$T_0 = 25^\circ\text{C}$ unless otherwise stated

Parameter	Symbol	Unit	Value	Notes
Data bit rate	G	Gbit/s	>25	
Operating wavelength	λ_{op}	nm	850 ± 15	$I_F = 8\text{mA}$
Threshold current	I_{th}	mA	<1	
Slope efficiency	η	W/A	>0.5	
Operating voltage	V_{op}	V	2.5	$I_F = 8\text{mA}$
Optical output power	P	mW	>3.5	$I_F = 8\text{mA}$
Differential resistance	R_s	Ω	<100	$I_F = 8\text{mA}$
-3dB modulation bandwidth	f_{3dB}	GHz	>15	$T_o = 20 - 85^\circ C$
Rise / Fall time	t_R	ps	<20	20% - 80%
Modulation current efficiency factor	MCEF	$\text{GHz}/\text{mA}^{1/2}$	>7	$T_o = 20 - 85^\circ C$
Wavelength temperature coefficient	$d\lambda/dT$	nm/ $^\circ C$	0.06	$T_o = 20 - 85^\circ C$
Thermal resistance	R_{th}	$^\circ C/\text{mW}$	<3.5	
RMS spectral width	$\Delta\lambda$	nm	<0.7	$I_F = 8\text{mA}$

T_o - operating temperature; I_F - operating current

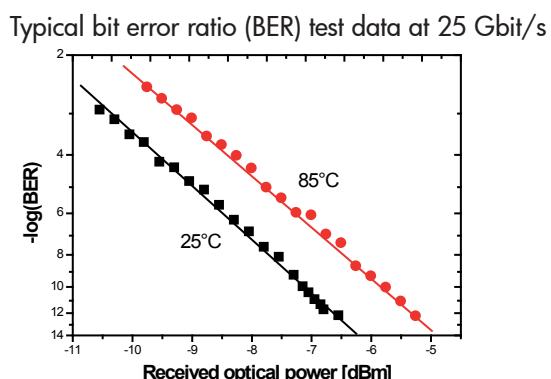
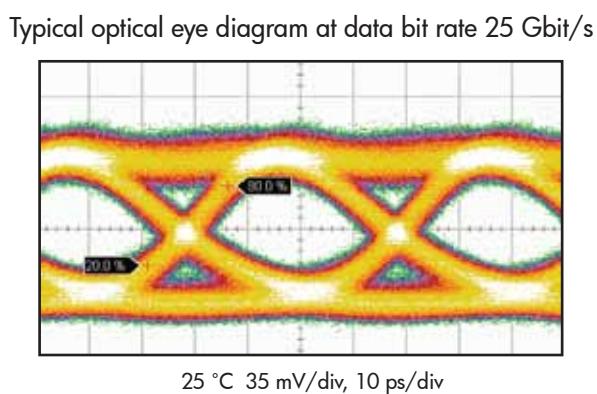
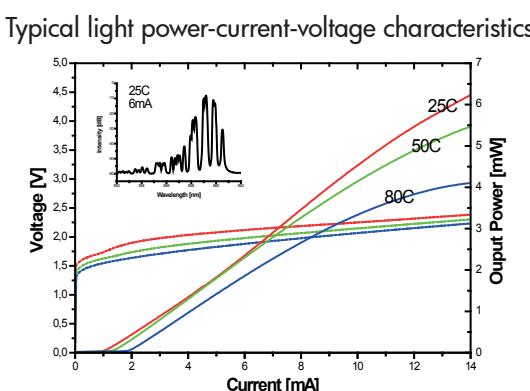
Absolute maximum ratings

Parameter	Symbol	Unit	Value
Forward current	I_{max}	mA	15
Reverse voltage	V_{rv}	V	5
Optical output power	P_{opt_max}	mW	7
Electrical dissipation power	P_{dis_max}	mW	35
Storage temperature	T_{st}	°C	-40 - 100

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Mechanical dimensions

Parameter	Unit	Value
Length (single VCSEL), L	μm	250
Length (1x4 VCSEL array), L	μm	1000
Length (1x12 VCSEL array), L	μm	3000
Width, W	μm	250
VCSEL pitch	μm	250
Thickness, H	μm	150
Au-bond pads	μm	80x80



Possible design of 1x4 VCSEL array:

